

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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Applicant: Tews et al.

Serial No.: 09/714,356

Filed: November 16, 2000

For: NITROGEN IMPLANTATION USING A SHADOW
EFFECT TO CONTROL GATE OXIDE THICKNESS
IN DRAM SEMICONDUCTOR

Art Unit: 2811

AUG -3 2001

Examiner: TBA

TECHNOLOGY CENTER 2801

Atty Dkt No: 00 P 9031 US

Batch No.: TBA

LETTER TO OFFICIAL DRAFTSMAN

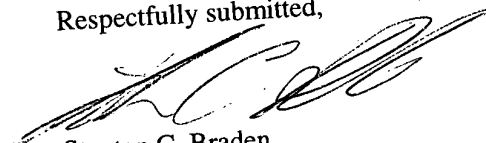
Attention: Drawing Processing Branch
Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

Pursuant to M.P.E.P. Section 608.02, enclosed please find two (2) sheets of formal drawings in the referenced case. These are formal versions of the informal drawings filed with the application.

If there are any informalities with these drawings, Applicant requests issuance of a Form PTO-948 identifying the informalities noted by the Official Draftsman.

Respectfully submitted,


Stanton C. Braden
Reg. No. 32,556


Date July 30, 2001

Infineon Technologies North America Corp.
c/o Siemens Corporation
Intellectual Property Department
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SCB/am

CERTIFICATE OF MAILING PURSUANT TO 37 CFR § 1.8

I hereby certify that this correspondence is being deposited on July 30, 2001 with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231 on or before the date below

Date of
Signature July 30, 2001


Pamela Gewirtz

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